

THE SPECIFICATION OF AlGaAs IR LED CHIP “YL-C660nM-20mcd”

1. DESCRIPTION

This is a AlGaAs red LED chip. It is N-side up.

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (Vf) IF=20mA		1.8		V
Reverse Voltage (Vr) IR=10uA	5			V
luminous intensity ¹⁾ (Iv) IF=20mA	20			mcd
Peak Wavelength (λp) IF=20mA	640	(660)	670	nm

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

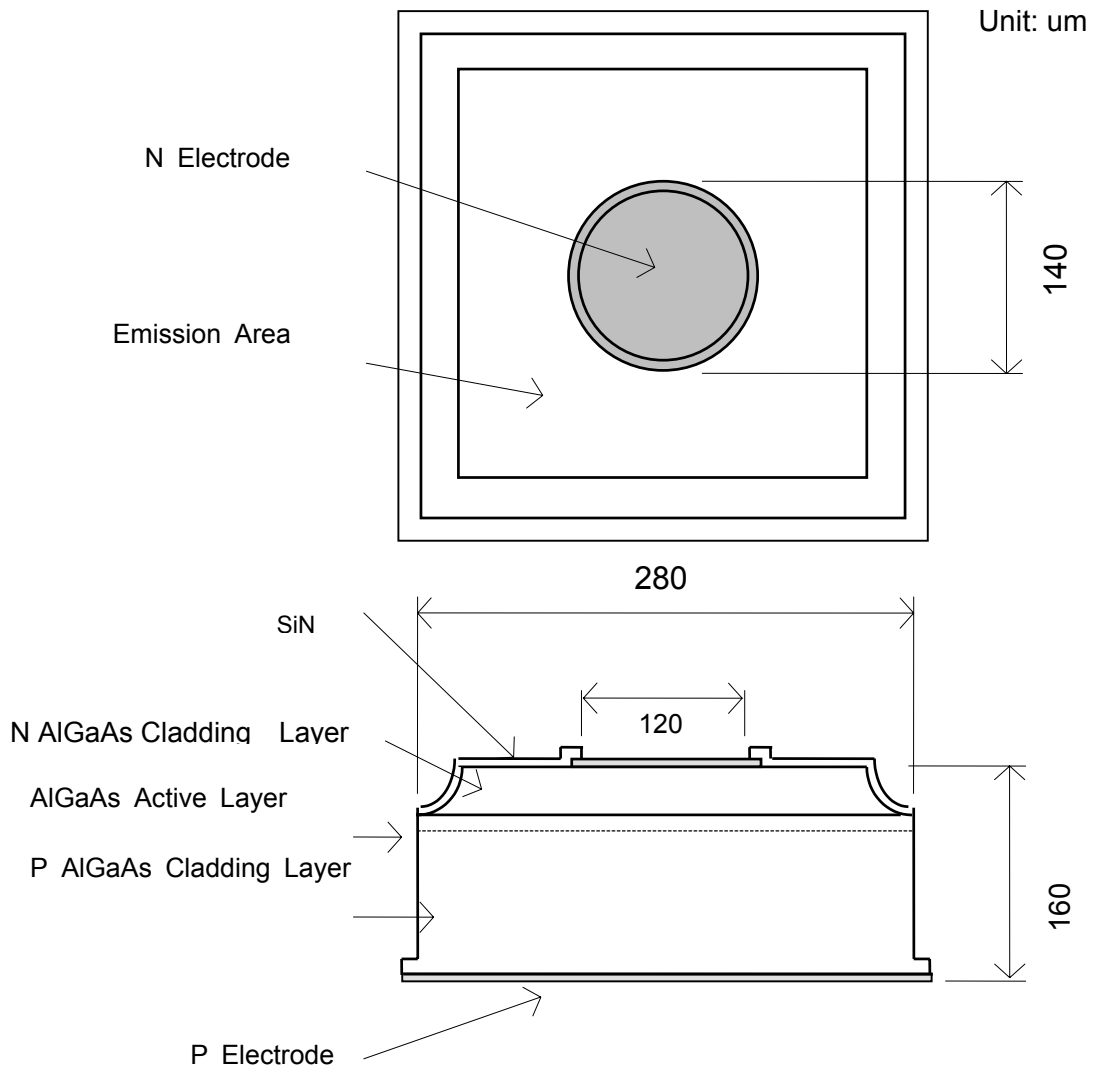
Continuous Maximum Forward Current	: 50 mA(DC)
Reverse Voltage	: 5 V(IR=10uA)
Storage Temperature	
while on mylar membrane	: 0 to 40 deg. C
after removal from mylar membrane	: -30 to 100 deg. C

4. PHYSICAL CHARACTERISTICS AND STRUCTURE

- 1) Material : AlGaAs
- 2) Structure : Double Hetero Structure
- 3) Junction Size : 0.280mm × 0.280mm
- 4) Thickness : 0.160mm
- 5) Bond Pad Size : 0.140mm diameter
- 6) Anode Metallization : Gold Alloy
- 7) Cathode Metallization : Gold Alloy

Physical Dimensions

Model YL-C660nM-20mcd



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.